

CLAIMS

1. A compound semiconductor substrate for epitaxial growth, wherein

when haze is defined as a value calculated by dividing intensity of scattered light obtained when light is incident from a predetermined light source onto a surface of a substrate, by intensity of the incident light from the light source,

the haze is not more than 2 ppm all over an effectively used area of the substrate and an off-angle with respect to a plane direction is 0.05 to 0.10° .

2. The compound semiconductor substrate as claimed in claim 1, wherein

the haze is not more than 1 ppm all over the effectively used area of the substrate.

3. The compound semiconductor substrate as claimed in claim 1 or 2, wherein

the compound semiconductor substrate is an InP substrate.

4. The compound semiconductor substrate as claimed in claim 3, wherein

a dislocation density is not more than $1000/\text{cm}^2$.

5. The compound semiconductor substrate as claimed in claim 4, wherein
the dislocation density is not more than $500/\text{cm}^2$.